Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	2276	(contact near9 ("IC" or (integrat\$4 near circuit))) and resin near9 ("IC" or (integrat\$4 near circuit))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2007/05/29 09:35
L3	1175	(contact near9 ("IC" or (integrat\$4 near circuit))) and resin near9 ("IC" or (integrat\$4 near circuit)) and (electric\$4 near connect\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/29 09:35
L4	487	(contact near9 ("IC" or (integrat\$4 near circuit))) and resin near9 ("IC" or (integrat\$4 near circuit)) and (electric\$4 near connect\$4) and (wir\$4 near bond\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/29 09:36
L5	9	(contact near9 ("IC" or (integrat\$4 near circuit))) and resin near9 ("IC" or (integrat\$4 near circuit)) and (electric\$4 near connect\$4) and (wir\$4 near bond\$4) and laminar	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/29 09:36
L6	190	(contact near9 ("IC" or (integrat\$4 near circuit))) and resin near9 ("IC" or (integrat\$4 near circuit)) and (electric\$4 near connect\$4) and (wir\$4 near bond\$4) and (flip near chip)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/29 10:01
L7	. 6	(contact near9 ("IC" or (integrat\$4 near circuit))) and resin near9 ("IC" or (integrat\$4 near circuit)) and (electric\$4 near connect\$4) and (wir\$4 near bond\$4) and (flip near chip) and (pressure near9 atmospher\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/29 10:18
L8	122	(wir\$4 near bond\$4) and (flip near chip) and (pressure near9 atmospher\$4) and mold\$4 and (hole or via or aperture or recess trench) near9 (substrate or wafer or carrier or base)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/29 10:20

L9	45	(wir\$4 near bond\$4) and (flip near chip) and (pressure near9 atmospher\$4) and mold\$4 and (hole or via or aperture or recess trench) near9 (substrate or wafer or carrier or base) and (resin or epoxy) near9 (hole or via or aperture or recess	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/29 10:21
S1	12	trench) (("6365963B1") or ("6038136") or ("5697148") or ("6121686") or ("6242279B1") or ("6130477") or ("6077724") or ("6024275")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/28 09:56
S2	0	S1 and (substrate or wafer or semiconductor) and connect\$4 and ("IC" or "integrated circuit") and resin.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/07/28 09:57
S3	43381	(substrate or wafer or semiconductor) and connect\$4 and ("IC" or "integrated circuit") and resin	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/28 09:58
S4	16355	(substrate or wafer or semiconductor) and connect\$4 and ("IC" or "integrated circuit") and resin and package	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/28 09:58
S5	347	(substrate or wafer or semiconductor) and connect\$4 and ("IC" or "integrated circuit") and resin and package and gas and pressure and (liquid near4 resin)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2006/07/28 09:59
S6	93	(substrate or wafer or semiconductor) and connect\$4 and ("IC" or "integrated circuit") and resin and package and gas and pressure and (liquid near4 resin) and "flip chip"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/28 09:59
S7	. 1	(substrate or wafer or semiconductor) and connect\$4 and ("IC" or "integrated circuit") and resin and package and gas and pressure and (liquid near4 resin) and "flip chip" and (contact or pad) and laminar	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2006/07/28 10:01

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S9	1	(substrate or wafer or semiconductor) and connect\$4 and ("IC" or "integrated circuit") and resin and package and gas and pressure and (liquid near4 resin) and "flip chip" and (contact or pad) and laminar and hole	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/28 10:02
S10	84	(substrate or wafer or semiconductor) and connect\$4 and ("IC" or "integrated circuit") and resin and package and gas and pressure and (liquid near4 resin) and "flip chip" and (contact or pad) and hole\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 10:51
S11	1604213	("IC" or "integrated circuit")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 10:51
S12	1239	("IC" or "integrated circuit") and (substrate or wafer or semiconductor) and connect\$4 and encas\$4 and resin	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 10:54
S13	996	("IC" or "integrated circuit") and (substrate or wafer or semiconductor) and connect\$4 and encas\$4 and resin and (hole or via or trench)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 10:56
S14	. 1	("IC" or "integrated circuit") and (substrate or wafer or semiconductor) and connect\$4 and encas\$4 and resin and (hole or via or trench) and box and gas and pressure and volume and (solder near ball) and (flip near4 chip) and wire and laminar	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 11:00
S15	1	("IC" or "integrated circuit") and (substrate or wafer or semiconductor) and connect\$4 and encas\$4 and resin and (hole or via or trench) and box and gas and pressure and volume and (solder near ball) and (flip near4 chip) and wire	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2006/08/01 11:00

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S16	16	("IC" or "integrated circuit") and (substrate or wafer or semiconductor) and connect\$4 and encas\$4 and resin and (hole or via or trench) and gas and pressure and volume and (solder near ball) and (flip near4 chip) and wire	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 11:31
S17	1	("IC" or "integrated circuit") and (substrate or wafer or semiconductor) and connect\$4 and encas\$4 and resin and (hole or via or trench) and gas and pressure and volume and (solder near ball) and (flip near4 chip) and wire and laminar	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2006/08/01 11:01
S18	669	("IC" or "integrated circuit") same (substrate or wafer or semiconductor) and connect\$4 and encas\$4 and resin and (hole or via or trench)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 11:31
S19	149	("IC" or "integrated circuit") same (substrate or wafer or semiconductor) and connect\$4 and encas\$4 and resin and (hole or via or trench) and (flip near chip)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 11:32
S20	2	("IC" or "integrated circuit") same (substrate or wafer or semiconductor) and connect\$4 and encas\$4 and resin and (hole or via or trench) and (flip near chip) and (laminar near8 substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 11:33
S21	149	("IC" or "integrated circuit") same (substrate or wafer or semiconductor) and connect\$4 and encas\$4 and resin and (hole or via or trench) and (flip near chip)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/17 07:42
S22	22	("IC" or "integrated circuit") same (substrate or wafer or semiconductor) and connect\$4 and encas\$4 and (liquid near4 resin) and (hole or via or trench) and (flip near chip)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 13:46
S23	26	("IC" or "integrated circuit") same (substrate or wafer or semiconductor) and connect\$4 and encas\$4 and (liquid near4 resin) and (hole or open\$3) and (flip near chip)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 13:47

S24	25	("IC" or "integrated circuit") near8 (substrate or wafer or semiconductor) and connect\$4 and encas\$4 and (liquid near4 resin) and (hole or open\$3) and (flip near chip)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 13:51
S25	4	("IC" or "integrated circuit") near8 (substrate or wafer or semiconductor) and connect\$4 and encas\$4 and (liquid near4 resin) and (hole or open\$3) and (flip near chip) and gas	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 14:09
S26	3	("integrated circuit" near8 substrate) and connect\$4 and encas\$4 and (liquid near4 resin) and (hole or open\$3) and (flip near chip) and gas	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2006/08/01 14:10
S27	21	("integrated circuit" near8 substrate) and connect\$4 and encas\$4 and (liquid near4 resin) and (hole or open\$3) and (flip near chip)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/02 10:44
S28	2777	encas\$4 near8 resin	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 14:13
S29	406	(encas\$4 near8 resin) and (liquid near4 resin)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 14:13
S30	65	(encas\$4 near8 resin) and (liquid near4 resin) and ("IC" or "integrated circuit")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 14:14
S31	38	(encas\$4 near8 resin) and (liquid near4 resin) and ("IC" or "integrated circuit") and (substrate or semiconductor or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 14:14

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S32	16	(encas\$4 near8 resin) and (liquid near4 resin) and ("IC" or "integrated circuit") and (substrate or semiconductor or wafer) and (flip near4 chip)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 14:15
S33	1	(encas\$4 near8 resin) and (liquid near4 resin) and ("IC" or "integrated circuit") and (substrate or semiconductor or wafer) and (flip near4 chip) and gas and solder	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 14:19
S34	11	(encas\$4 near8 resin) and (liquid near4 resin) and ("IC" or "integrated circuit") and (substrate or semiconductor or wafer) and (flip near4 chip) and solder	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 14:20
S35	8	(encas\$4 near8 resin) and (liquid near4 resin) and ("IC" or "integrated circuit") and (substrate or semiconductor or wafer) and (flip near4 chip) and solder and (hole\$2 or open\$3 or via)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/01 14:20
S36	12	(("6365963B1") or ("6038136") or ("5697148") or ("6121686") or ("6242279B1") or ("6130477") or ("6077724") or ("6024275")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/02 07:22
S37	1	(substrate near8 hole\$2) and encas\$4 and resin and box and gas and mold\$4 and pressure and volume and (laminar near8 substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/02 10:48
S38	1	(substrate near8 hole\$2) and encas\$4 and resin and pressure and volume and (laminar near8 substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/02 10:48
S39	. 13	(substrate near8 hole\$2) and encas\$4 and resin and (laminar near8 substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/02 10:48

S40	6	(substrate near8 hole\$2) and encas\$4 and resin and (laminar near8 substrate) and box	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/02 10:49
S41	6	(substrate near8 hole\$2) and encas\$4 and resin and (laminar near8 substrate) and box and gas	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/02 10:49
S42	6	(substrate near8 hole\$2) and encas\$4 and resin and (laminar near8 substrate) and box and gas and pressure	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/02 10:49
S43	6	(substrate near8 hole\$2) and encas\$4 and resin and (laminar near8 substrate) and box and gas and pressure and (solder near4 ball)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2006/08/02 10:49
S44	1	(substrate near8 hole\$2) and encas\$4 and resin and (laminar near8 substrate) and box and gas and pressure and (solder near4 ball) and (flip near4 chip)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2006/08/02 10:50
S45	6	(substrate near8 hole\$2) and encas\$4 and resin and (laminar near8 substrate) and box and gas and pressure and (solder near4 ball) and (recess or indent)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/02 10:50
S46	21198	(("IC" or (integrated near circuit)) near9 (substrate or wafer or semiconductor or carrier)) and interconnect and ((pad or contact) near9 (substrate or wafer or semiconductor or carrier))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/17 10:51
S47	8755	(("IC" or (integrated near circuit)) near9 (substrate or wafer or semiconductor or carrier)) and interconnect and ((pad or contact) near9 (substrate or wafer or semiconductor or carrier)) and package	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/17 10:52

· S48	26	(("IC" or (integrated near circuit)) near9 (substrate or wafer or semiconductor or carrier)) and interconnect and ((pad or contact) near9 (substrate or wafer or semiconductor or carrier)) and package and (encas\$4 near9 resin)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2007/04/17 10:52
S49	18	(("IC" or (integrated near circuit)) near9 (substrate or wafer or semiconductor or carrier)) and interconnect and ((pad or contact) near9 (substrate or wafer or semiconductor or carrier)) and package and (encas\$4 near9 resin) and (flip near chip)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/17 11:09
S50	14	(("IC" or (integrated near circuit)) near9 (substrate or wafer or semiconductor or carrier)) and interconnect and ((pad or contact) near9 (substrate or wafer or semiconductor or carrier)) and package and (encas\$4 near9 resin) and ((flip near chip) near9 (substrate or wafer or semiconductor or carrier))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/17 11:23
S51	13019	(("IC" or (integrated near circuit)) near9 (substrate or wafer or semiconductor or carrier)) and (flip near chip)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/17 11:23
S52	43	(("IC" or (integrated near circuit)) near9 (substrate or wafer or semiconductor or carrier)) and (flip near chip) and (encas\$4 near9 resin)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/17 11:34
S53	4526	(("IC" or (integrated near circuit)) near9 (substrate or wafer or semiconductor or carrier)) and (flip near chip) and resin	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/17 11:36

S54	17	(("IC" or (integrated near circuit)) near9 (substrate or wafer or semiconductor or carrier)) and (flip near chip) and resin and (laminar near9 (substrate or wafer or semiconductor or carrier))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/17 11:36
S55	80601	packag\$4 and circuit\$2 and (connect\$4 near9 (substrate or wafer or base or carrier))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/17 07:43
S56	651	packag\$4 and circuit\$2 and (connect\$4 near9 (substrate or wafer or base or carrier)) and ((encas\$4 or enclos\$4) near9 resin)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/17 07:45
S57	5	packag\$4 and circuit\$2 and (connect\$4 near9 (substrate or wafer or base or carrier)) and ((encas\$4 or enclos\$4) near9 resin) and (laminar near9 (substrate or wafer or carrier or base))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/17 07:46
S58	5	packag\$4 and circuit\$2 and (connect\$4 near9 (substrate or wafer or base or carrier)) and ((encas\$4 or enclos\$4) near9 resin) and (laminar near9 (substrate or wafer or carrier or base)) and (flip near chip)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/17 07:46
S59	5	packag\$4 and circuit\$2 and (connect\$4 near9 (substrate or wafer or base or carrier)) and ((encas\$4 or enclos\$4) near9 resin) and (laminar near9 (substrate or wafer or carrier or base)) and (flip near chip) and contact	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/17 07:46
S60		packag\$4 and circuit\$2 and (connect\$4 near9 (substrate or wafer or base or carrier)) and ((encas\$4 or enclos\$4) near9 resin) and (laminar near9 (substrate or wafer or carrier or base)) and (flip near chip) and contact and (solder near ball)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/17 07:48

S61		packag\$4 and circuit\$2 and (connect\$4 near9 (substrate or wafer or base or carrier)) and ((encas\$4 or enclos\$4) near9 resin) and laminar and (flip near chip) and contact and (solder near ball)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/17 07:49
S62	. 3	packag\$4 and circuit\$2 and (connect\$4 near9 (substrate or wafer or base or carrier)) and ((encas\$4 or enclos\$4) near9 resin) and laminar and (solder near ball)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/17 07:50
S63	3	packag\$4 and circuit\$2 and (wir\$3 near9 (substrate or wafer or base or carrier)) and ((encas\$4 or enclos\$4) near9 resin) and laminar and (solder near ball)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/17 07:50
S64	0	packag\$4 and circuit\$2 and (electrical near connect) and (substrate or wafer or base or carrier) and ((encas\$4 or enclos\$4) near9 resin) and laminar and (solder near ball)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/17 07:54
S65	3	packag\$4 and circuit\$2 and (electrical near9 connect\$4) and (substrate or wafer or base or carrier) and ((encas\$4 or enclos\$4) near9 resin) and laminar and (solder near ball)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/17 07:55
S66	3	packag\$4 and circuit\$2 and connect\$4 and (substrate or wafer or base or carrier) and ((encas\$4 or enclos\$4) near9 resin) and laminar and (solder near ball)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/17 07:56
S67	3	packag\$4 and circuit\$2 and connect\$4 and (substrate or wafer or base or carrier) and ((encas\$4 or enclos\$4) near9 resin) and laminar and (solder near9 ball)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/17 07:56
S68	16	packag\$4 and circuit\$2 and connect\$4 and (substrate or wafer or base or carrier) and (encas\$4 or enclos\$4) and resin and laminar and (solder near9 ball)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/29 09:34